

- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

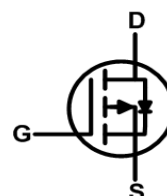
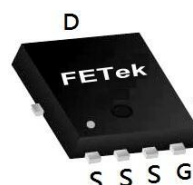
Product Summary


BVDSS	RDSON	ID
-30V	8.7mΩ	-50A

Description

The FKBB3115 is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The FKBB3115 meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

PRPAK3X3 Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	±25	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, V_{GS} @ -10V ¹	-50	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current, V_{GS} @ -10V ¹	-32	A
I_{DM}	Pulsed Drain Current ²	-200	A
EAS	Single Pulse Avalanche Energy ³	125	mJ
I_{AS}	Avalanche Current	-50	A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation ⁴	69	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	65	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	1.8	°C/W

**Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=-250\mu A$	-30	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V$, $I_D=-20A$	---	7.3	8.7	$m\Omega$
		$V_{GS}=-4.5V$, $I_D=-15A$	---	11	13.5	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250\mu A$	-1.0	---	-2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-24V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	-1	μA
		$V_{DS}=-24V$, $V_{GS}=0V$, $T_J=55^\circ\text{C}$	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 25V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-5V$, $I_D=-20A$	---	25	---	S
Q_g	Total Gate Charge (-4.5V)	$V_{DS}=-15V$, $V_{GS}=-4.5V$, $I_D=-15A$	---	30	---	nC
Q_{gs}	Gate-Source Charge		---	10	---	
Q_{gd}	Gate-Drain Charge		---	10.4	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-15V$, $V_{GS}=-10V$, $R_G=3.3\Omega$ $I_D=-15A$	---	9.4	---	ns
T_r	Rise Time		---	10.2	---	
$T_{d(off)}$	Turn-Off Delay Time		---	117	---	
T_f	Fall Time		---	24	---	
C_{iss}	Input Capacitance	$V_{DS}=-15V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	3448	---	pF
C_{oss}	Output Capacitance		---	508	---	
C_{rss}	Reverse Transfer Capacitance		---	421	---	

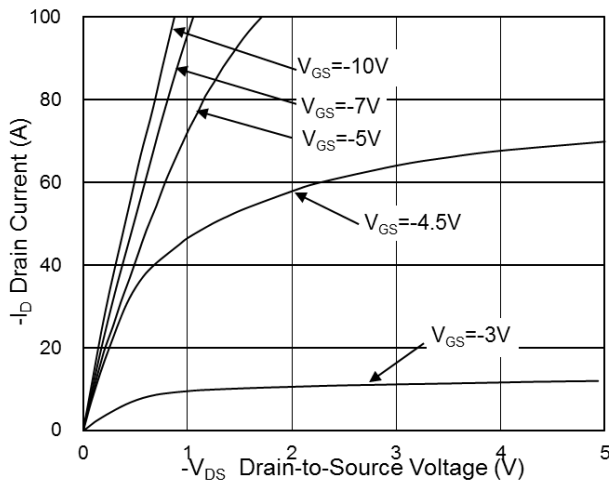
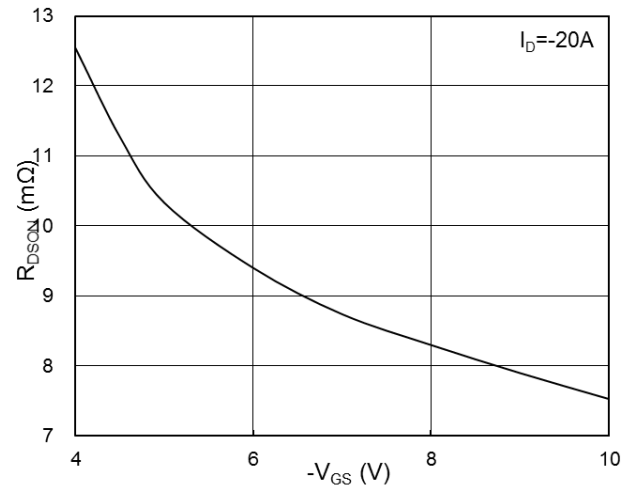
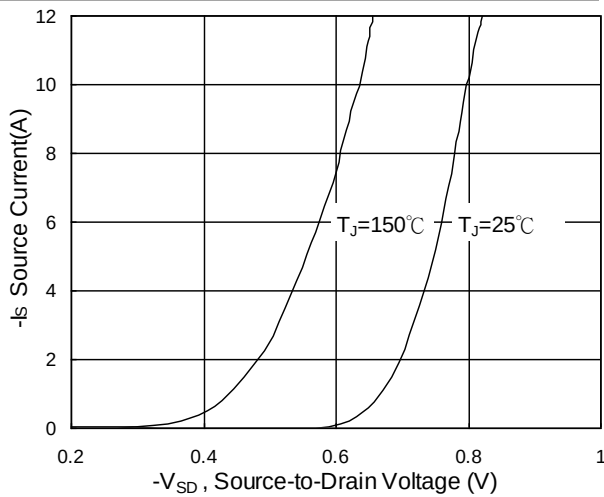
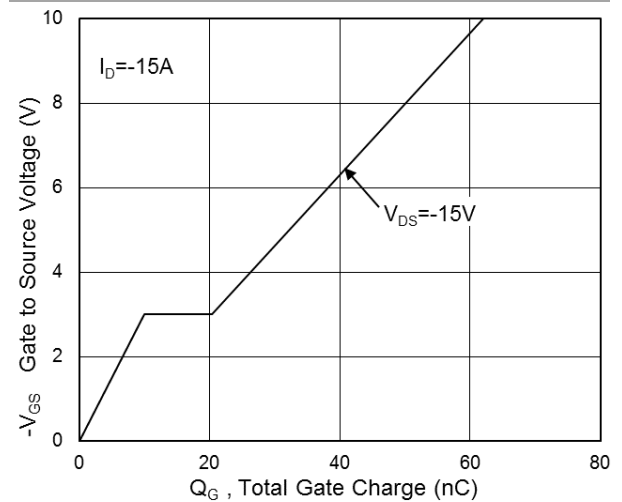
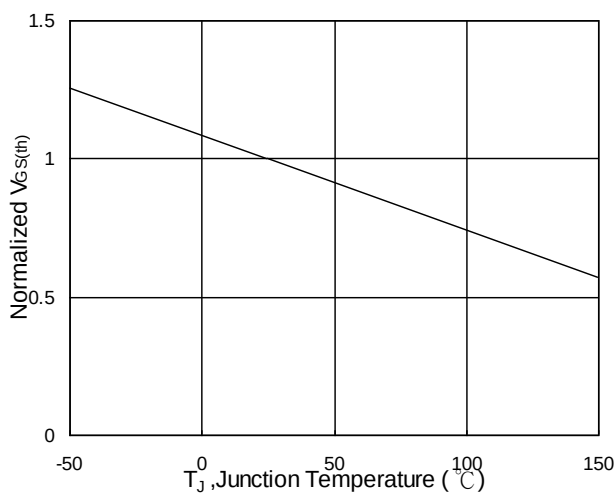
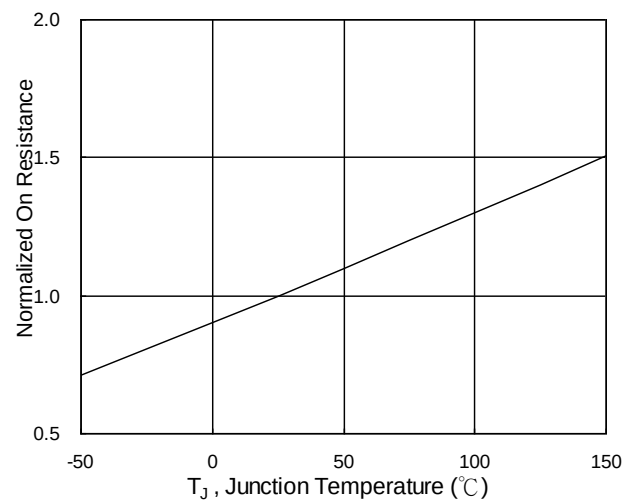
Diode Characteristics

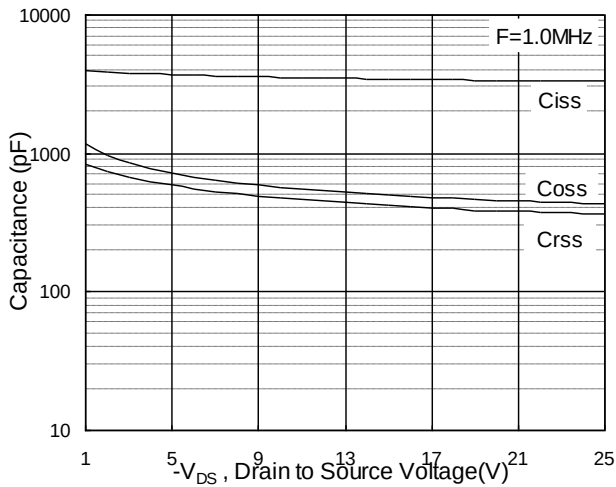
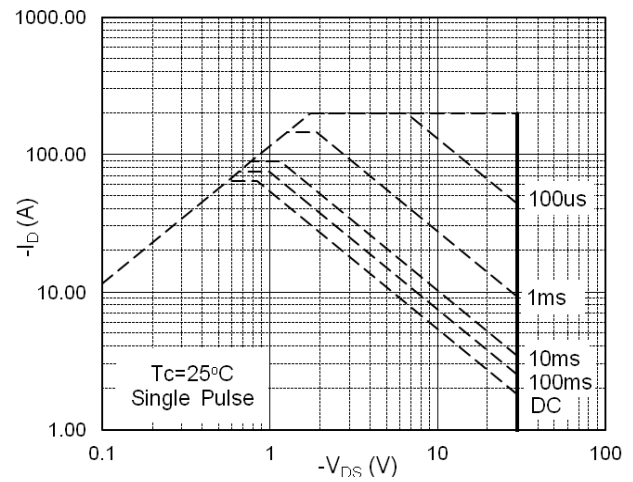
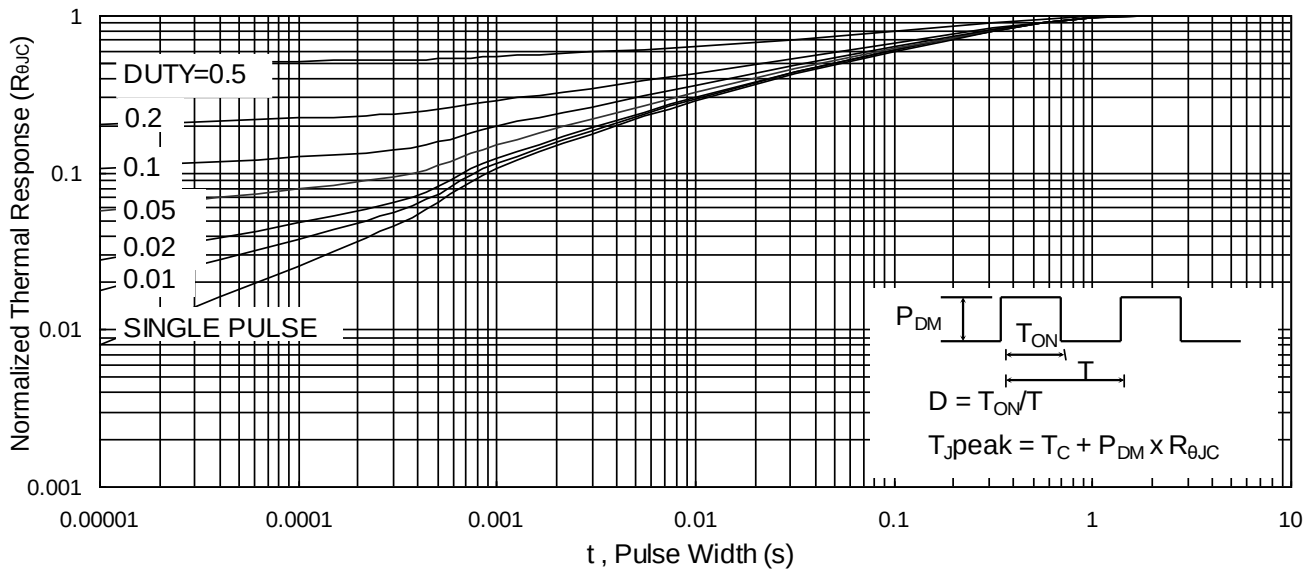
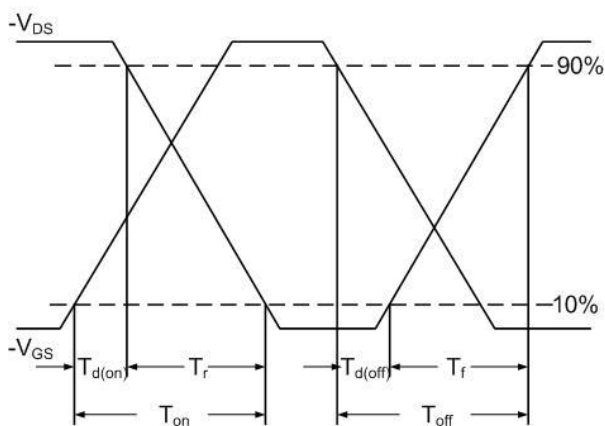
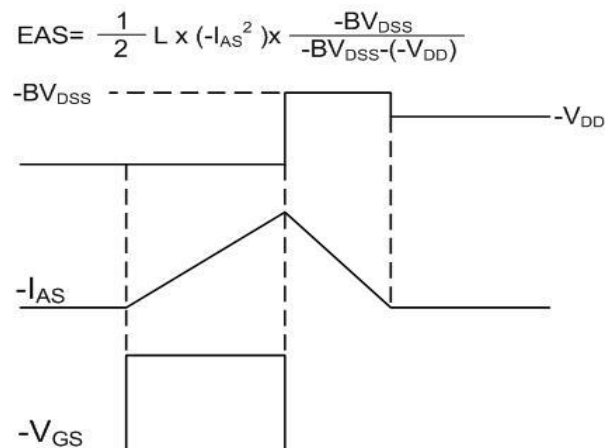
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	-50	A
I_{SM}	Pulsed Source Current ²		---	---	-130	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=-1A$, $T_J=25^\circ\text{C}$	---	---	-1	V
t_{rr}	Reverse Recovery Time	$I_F=-15A$, $di/dt=100A/\mu s$, $T_J=25^\circ\text{C}$	---	20	---	nS
Q_{rr}	Reverse Recovery Charge		---	9.5	---	nC

Note :

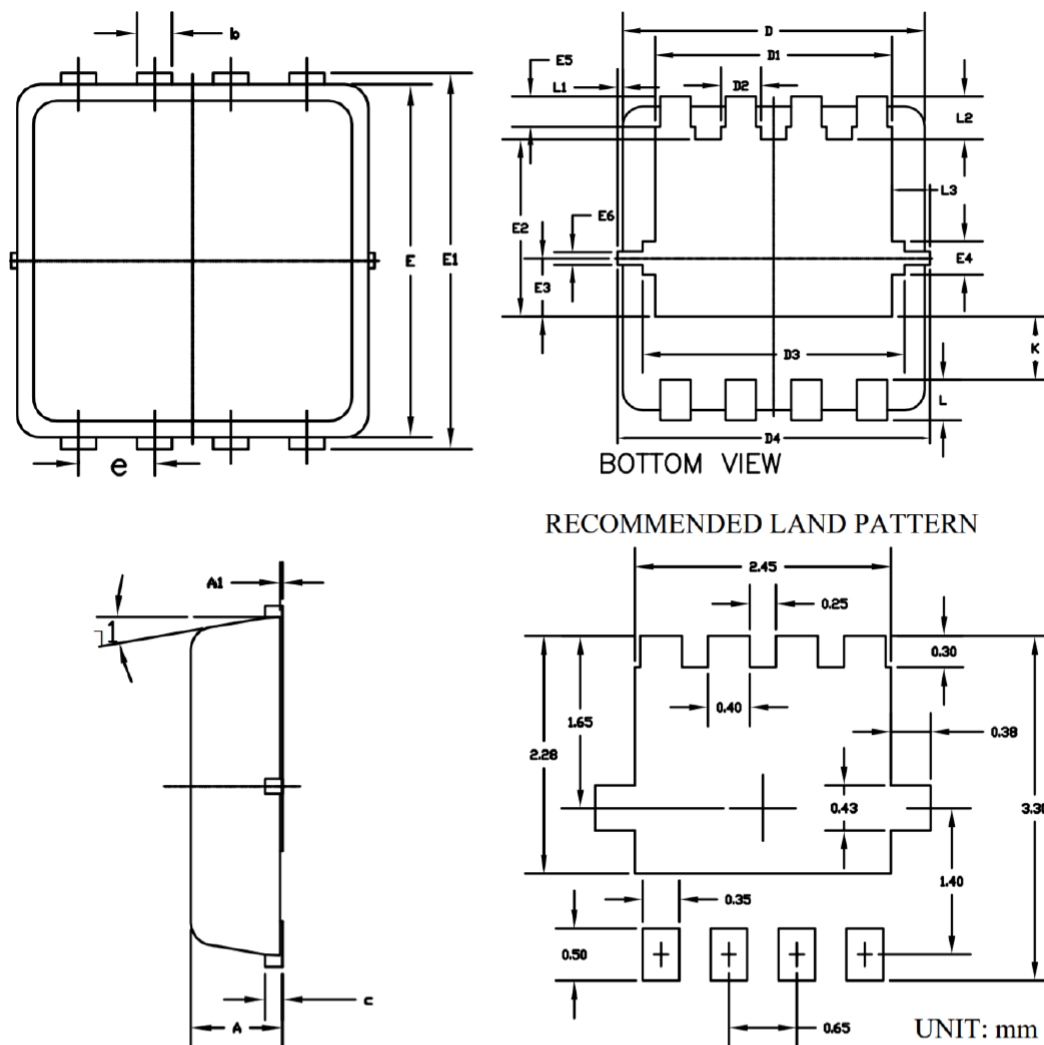
- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=-25V$, $V_{GS}=-10V$, $L=0.1mH$, $I_{AS}=-50A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D , in real applications , should be limited by total power dissipation.

Typical Characteristics


Fig.1 Typical Output Characteristics

Fig.2 On-Resistance vs G-S Voltage

Fig.3 Source Drain Forward Characteristics

Fig.4 Gate-Charge Characteristics

Fig.5 Normalized $V_{GS(th)}$ vs T_J

Fig.6 Normalized $R_{DS(on)}$ vs T_J


Fig.7 Capacitance

Fig.8 Safe Operating Area

Fig.9 Normalized Maximum Transient Thermal Impedance

Fig.10 Switching Time Waveform

Fig.11 Unclamped Inductive Switching Waveform

PRPAK3X3 Package Outline Dimensions



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.80	0.90	0.028	0.031	0.035
A1	0.00		0.05	0.000		0.002
b	0.24	0.30	0.35	0.009	0.012	0.014
c	0.10	0.15	0.25	0.004	0.006	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
D1	2.25	2.35	2.45	0.089	0.093	0.097
D2	0.30	0.40	0.50	0.012	0.016	0.020
D3	2.50	2.60	2.70	0.098	0.102	0.106
D4	3.00	3.10	3.20	0.118	0.122	0.126
E	2.90	3.00	3.10	0.114	0.118	0.122
E1	3.10	3.20	3.30	0.122	0.126	0.130
E2	1.65	1.75	1.85	0.065	0.069	0.073
E3	0.48	0.58	0.68	0.019	0.023	0.027
E4	0.23	0.33	0.43	0.009	0.013	0.017
E5	0.20	0.30	0.40	0.008	0.012	0.016
E6	0.075	0.125	0.175	0.003	0.005	0.007
e	0.60	0.65	0.70	0.024	0.026	0.028
K	0.52	0.62	0.72	0.020	0.024	0.028
L	0.30	0.40	0.50	0.012	0.016	0.020
L1	0	0.05	0.10	0	0.002	0.004
L2	0.33	0.43	0.53	0.013	0.017	0.021
L3	0.275	0.375	0.475	0.011	0.015	0.019
γ1	0°	10°	12°	0°	10°	12°

Marking Instruction

